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Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	SIO, UART/USART
Peripherals	LED, POR, Voltage Detect, WDT
Number of I/O	13
Program Memory Size	4KB (4K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	384 x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	-
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	20-LSSOP (0.173", 4.40mm Width)
Supplier Device Package	20-LSSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21191sp-u0

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1.3 Block Diagram

Figure 1.1 shows a Block Diagram.

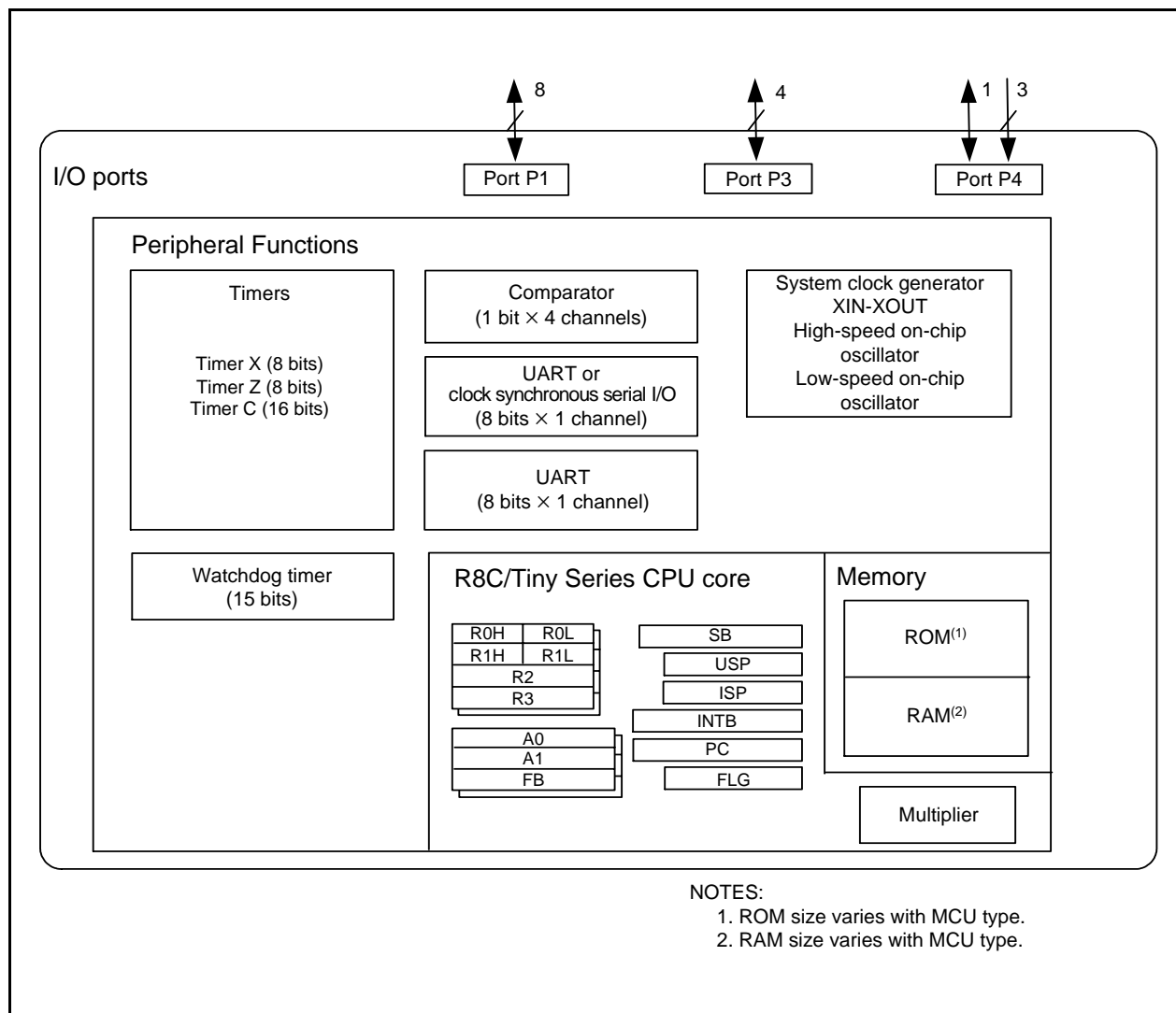


Figure 1.1 Block Diagram

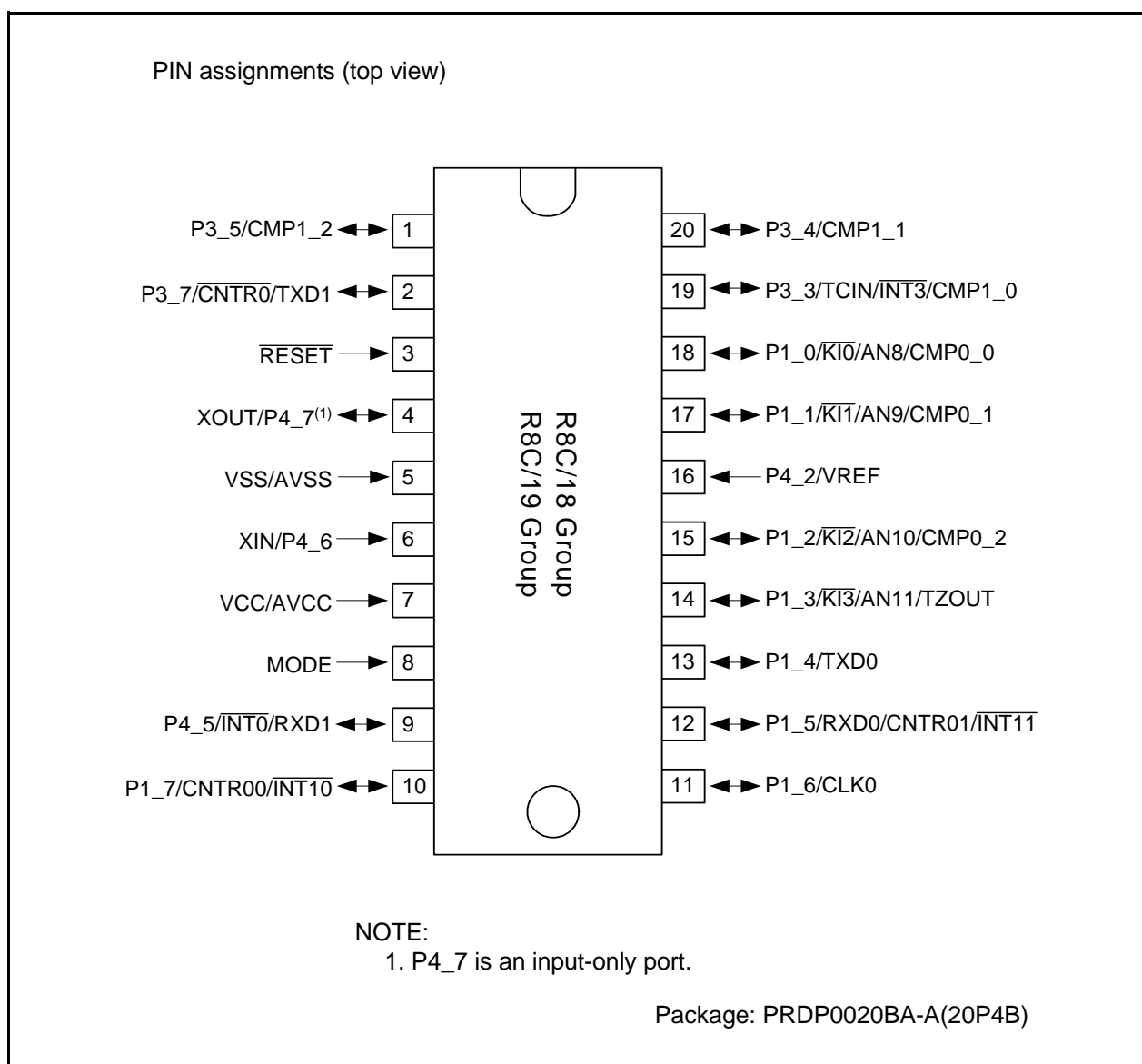


Figure 1.5 Pin Assignments for PRDP0020BA-A Package (Top View)

Table 1.7 Pin Name Information by Pin Number of PWQN0028KA-B package

Pin Number	Control Pin	Port	I/O Pin of Peripheral Function			
			Interrupt	Timer	Serial Interface	Comparator
1	NC					
2	XOUT	P4_7				
3	VSS/AVSS					
4	NC					
5	NC					
6	XIN	P4_6				
7	NC					
8	VCC/AVCC					
9	MODE					
10		P4_5	$\overline{\text{INT0}}$		RXD1	
11		P1_7	$\overline{\text{INT10}}$	CNTR00		
12		P1_6			CLK0	
13		P1_5	$\overline{\text{INT11}}$	CNTR01	RXD0	
14		P1_4			TXD0	
15	NC					
16		P1_3	$\overline{\text{KI3}}$	TZOUT		AN11
17		P1_2	$\overline{\text{KI2}}$	CMP0_2		AN10
18	NC					
19	NC					
20	VREF	P4_2				
21	NC					
22		P1_1	$\overline{\text{KI1}}$	CMP0_1		AN9
23		P1_0	$\overline{\text{KI0}}$	CMP0_0		AN8
24		P3_3	$\overline{\text{INT3}}$	TCIN/CMP1_0		
25		P3_4		CMP1_1		
26		P3_5		CMP1_2		
27		P3_7		$\overline{\text{CNTR0}}$	TXD1	
28	$\overline{\text{RESET}}$					

2.8.7 Interrupt Enable Flag (I)

The I flag enables maskable interrupts.

Interrupts are disabled when the I flag is set to 0, and are enabled when the I flag is set to 1. The I flag is set to 0 when an interrupt request is acknowledged.

2.8.8 Stack Pointer Select Flag (U)

ISP is selected when the U flag is set to 0; USP is selected when the U flag is set to 1.

The U flag is set to 0 when a hardware interrupt request is acknowledged or the INT instruction of software interrupt numbers 0 to 31 is executed.

2.8.9 Processor Interrupt Priority Level (IPL)

IPL is 3 bits wide, assigns processor interrupt priority levels from level 0 to level 7.

If a requested interrupt has higher priority than IPL, the interrupt is enabled.

2.8.10 Reserved Bit

If necessary, set to 0. When read, the content is undefined.

3. Memory

3.1 R8C/18 Group

Figure 3.1 is a Memory Map of R8C/18 Group. The R8C/18 Group has 1 Mbyte of address space from addresses 00000h to FFFFFh.

The internal ROM area is allocated lower addresses, beginning with address 0C000h. For example, a 16-Kbyte internal ROM is allocated addresses 0C000h to 0FFFFh.

The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.

The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 1-Kbyte internal RAM area is allocated addresses 00400h to 007FFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.

Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.

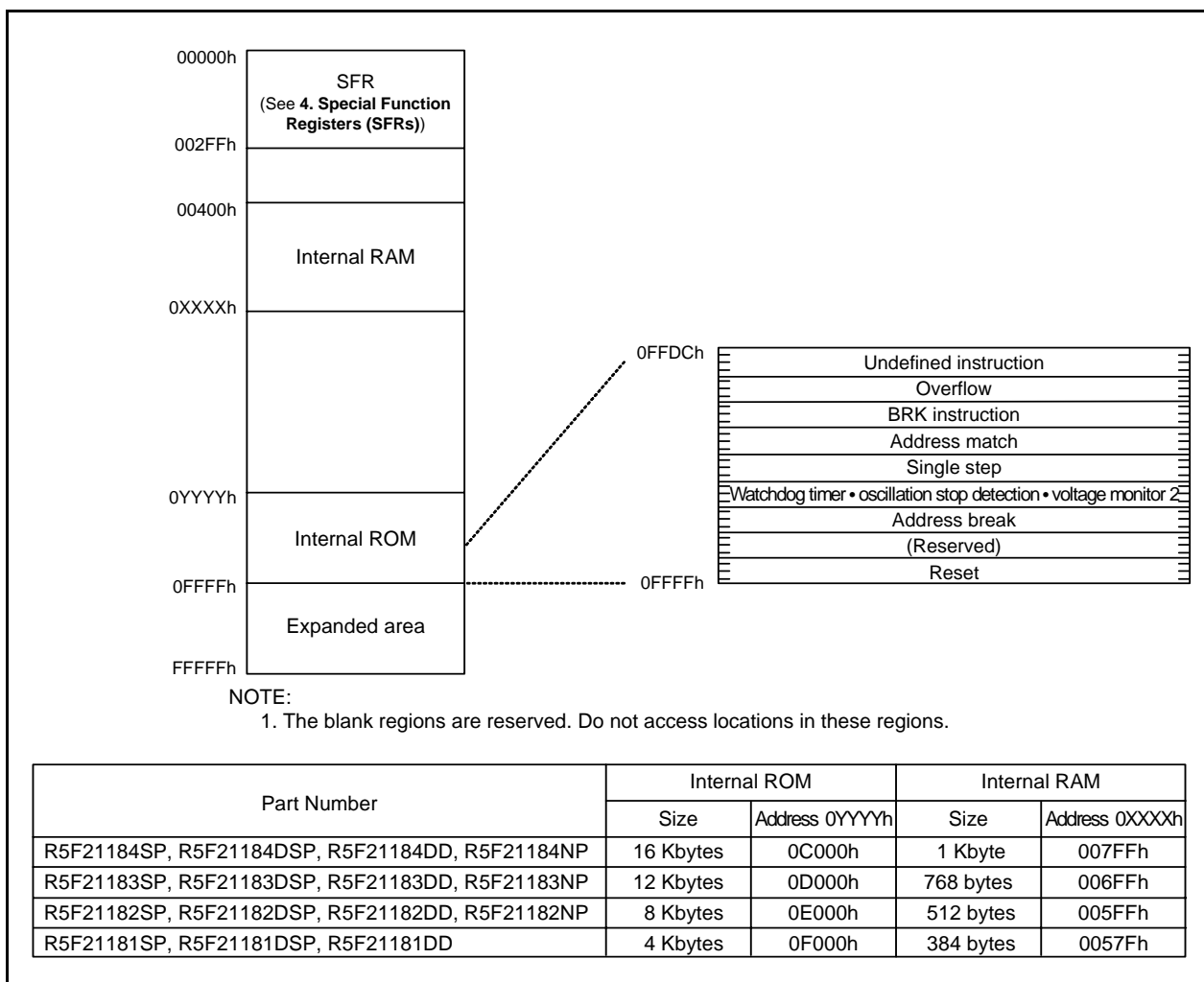


Figure 3.1 Memory Map of R8C/18 Group

3.2 R8C/19 Group

Figure 3.2 is a Memory Map of R8C/19 Group. The R8C/19 group has 1 Mbyte of address space from addresses 00000h to FFFFFh.

The internal ROM (program ROM) is allocated lower addresses, beginning with address 0FFFFh. For example, a 16-Kbyte internal ROM area is allocated addresses 0C000h to 0FFFFh.

The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.

The internal ROM (data flash) is allocated addresses 02400h to 02BFFh.

The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 1-Kbyte internal RAM area is allocated addresses 00400h to 007FFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.

Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.

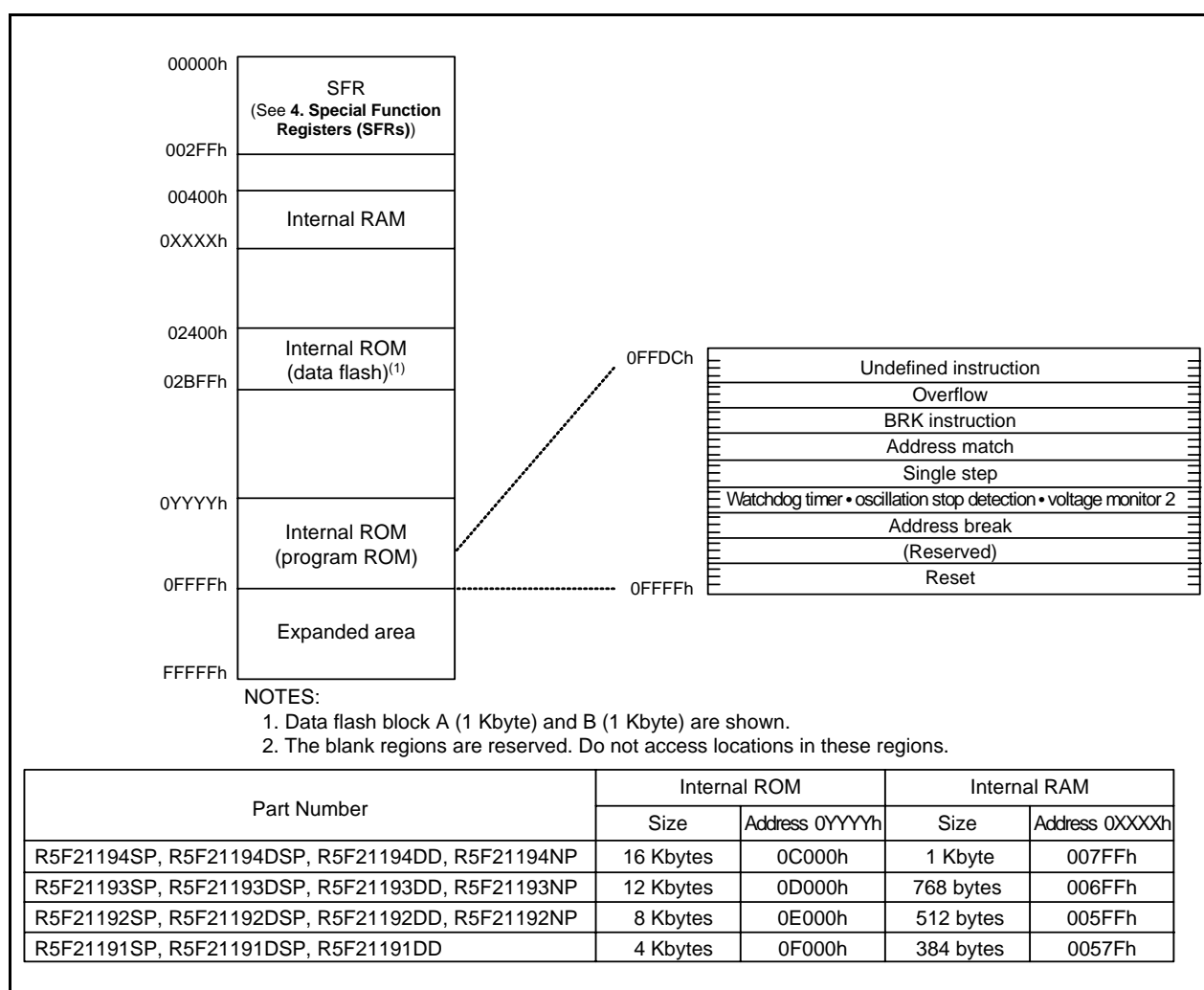


Figure 3.2 Memory Map of R8C/19 Group

4. Special Function Registers (SFRs)

An SFR (special function register) is a control register for a peripheral function. Tables 4.1 to 4.4 list the special function registers.

Table 4.1 SFR Information (1)(1)

Address	Register	Symbol	After reset
0000h			
0001h			
0002h			
0003h			
0004h	Processor Mode Register 0	PM0	00h
0005h	Processor Mode Register 1	PM1	00h
0006h	System Clock Control Register 0	CM0	01101000b
0007h	System Clock Control Register 1	CM1	00100000b
0008h			
0009h	Address Match Interrupt Enable Register	AIER	00h
000Ah	Protect Register	PRCR	00h
000Bh			
000Ch	Oscillation Stop Detection Register	OSD	00000100b
000Dh	Watchdog Timer Reset Register	WDTR	XXh
000Eh	Watchdog Timer Start Register	WDTS	XXh
000Fh	Watchdog Timer Control Register	WDC	00011111b
0010h	Address Match Interrupt Register 0	RMAD0	00h
0011h			00h
0012h			X0h
0013h			
0014h	Address Match Interrupt Register 1	RMAD1	00h
0015h			00h
0016h			X0h
0017h			
0018h			
0019h			
001Ah			
001Bh			
001Ch	Count Source Protection Mode Register	CSPR	00h
001Dh			
001Eh	INT0 Input Filter Select Register	INT0F	00h
001Fh			
0020h	High-Speed On-Chip Oscillator Control Register 0	HRA0	00h
0021h	High-Speed On-Chip Oscillator Control Register 1	HRA1	When shipping
0022h	High-Speed On-Chip Oscillator Control Register 2	HRA2	00h
0023h			
0024h			
0025h			
0026h			
0027h			
0028h			
0029h			
002Ah			
002Bh			
002Ch			
002Dh			
002Eh			
002Fh			
0030h			
0031h	Voltage Detection Register 1 ⁽²⁾	VCA1	00001000b
0032h	Voltage Detection Register 2 ⁽²⁾	VCA2	00h ⁽³⁾ 01000000b ⁽⁴⁾
0033h			
0034h			
0035h			
0036h	Voltage Monitor 1 Circuit Control Register ⁽²⁾	VW1C	0000X000b ⁽³⁾ 0100X001b ⁽⁴⁾
0037h	Voltage Monitor 2 Circuit Control Register ⁽⁵⁾	VW2C	00h
0038h			
0039h			
003Ah			
003Bh			
003Ch			
003Dh			
003Eh			
003Fh			

X: Undefined

NOTES:

1. The blank regions are reserved. Do not access locations in these regions.
2. Software reset, watchdog timer reset, and voltage monitor 2 reset do not affect this register.
3. After hardware reset.
4. After power-on reset or voltage monitor 1 reset.
5. Software reset, watchdog timer reset, and voltage monitor 2 reset do not affect b2 and b3.

Table 4.3 SFR Information (3)(1)

Address	Register	Symbol	After reset
0080h	Timer Z Mode Register	TZMR	00h
0081h			
0082h			
0083h			
0084h	Timer Z Waveform Output Control Register	PUM	00h
0085h	Prescaler Z Register	PREZ	FFh
0086h	Timer Z Secondary Register	TZSC	FFh
0087h	Timer Z Primary Register	TZPR	FFh
0088h			
0089h			
008Ah	Timer Z Output Control Register	TZOC	00h
008Bh	Timer X Mode Register	TXMR	00h
008Ch	Prescaler X Register	PREX	FFh
008Dh	Timer X Register	TX	FFh
008Eh	Timer Count Source Setting Register	TCSS	00h
008Fh			
0090h	Timer C Register	TC	00h
0091h			00h
0092h			
0093h			
0094h			
0095h			
0096h	External Input Enable Register	INTEN	00h
0097h			
0098h	Key Input Enable Register	KIEN	00h
0099h			
009Ah	Timer C Control Register 0	TCC0	00h
009Bh	Timer C Control Register 1	TCC1	00h
009Ch	Capture, Compare 0 Register	TM0	00h
009Dh			00h ⁽²⁾
009Eh	Compare 1 Register	TM1	FFh
009Fh			FFh
00A0h	UART0 Transmit/Receive Mode Register	U0MR	00h
00A1h	UART0 Bit Rate Register	U0BRG	XXh
00A2h	UART0 Transmit Buffer Register	U0TB	XXh
00A3h			XXh
00A4h	UART0 Transmit/Receive Control Register 0	U0C0	00001000b
00A5h	UART0 Transmit/Receive Control Register 1	U0C1	00000010b
00A6h	UART0 Receive Buffer Register	U0RB	XXh
00A7h			XXh
00A8h	UART1 Transmit/Receive Mode Register	U1MR	00h
00A9h	UART1 Bit Rate Register	U1BRG	XXh
00AAh	UART1 Transmit Buffer Register	U1TB	XXh
00ABh			XXh
00ACh	UART1 Transmit/Receive Control Register 0	U1C0	00001000b
00ADh	UART1 Transmit/Receive Control Register 1	U1C1	00000010b
00AEh	UART1 Receive Buffer Register	U1RB	XXh
00AFh			XXh
00B0h	UART Transmit/Receive Control Register 2	U0CON	00h
00B1h			
00B2h			
00B3h			
00B4h			
00B5h			
00B6h			
00B7h			
00B8h			
00B9h			
00BAh			
00BBh			
00BCh			
00BDh			
00BEh			
00BFh			

X: Undefined

NOTES:

1. The blank regions are reserved. Do not access locations in these regions.
2. When the output compare mode is selected (the TCC13 bit in the TCC1 register = 1), the value is set to FFFF₁₆.

Table 4.4 SFR Information (4)(1)

Address	Register	Symbol	After reset
00C0h	A/D Register	AD	XXh
00C1h			
00C2h			
00C3h			
00C4h			
00C5h			
00C6h			
00C7h			
00C8h			
00C9h			
00CAh			
00CBh			
00CCh			
00CDh			
00CEh			
00CFh			
00D0h	A/D Control Register 2	ADCON2	00h
00D1h			
00D2h			
00D3h			
00D4h			
00D5h			
00D6h			
00D7h			
00D8h			
00D9h			
00DAh			
00DBh			
00DCh			
00DDh			
00DEh			
00DFh			
00E0h	A/D Control Register 0	ADCON0	00000XXXb
00E1h			
00E2h			
00E3h			
00E4h			
00E5h			
00E6h			
00E7h			
00E8h			
00E9h			
00EAh			
00EBh			
00ECh			
00EDh			
00EEh			
00EFh			
00F0h	A/D Control Register 1	ADCON1	00h
00F1h			
00F2h			
00F3h			
00F4h			
00F5h			
00F6h			
00F7h			
00F8h			
00F9h			
00FAh			
00FBh			
00FCh			
00FDh			
00FEh			
00FFh			
00E0h	Port P1 Register	P1	XXh
00E1h			
00E2h			
00E3h			
00E4h			
00E5h			
00E6h			
00E7h			
00E8h			
00E9h			
00EAh			
00EBh			
00ECh			
00EDh			
00EEh			
00EFh			
00F0h	Port P1 Direction Register	PD1	00h
00F1h			
00F2h			
00F3h			
00F4h			
00F5h			
00F6h			
00F7h			
00F8h			
00F9h			
00FAh			
00FBh			
00FCh			
00FDh			
00FEh			
00FFh			
00E0h	Port P3 Register	P3	XXh
00E1h			
00E2h			
00E3h			
00E4h			
00E5h			
00E6h			
00E7h			
00E8h			
00E9h			
00EAh			
00EBh			
00ECh			
00EDh			
00EEh			
00EFh			
00F0h	Port P3 Direction Register	PD3	00h
00F1h			
00F2h			
00F3h			
00F4h			
00F5h			
00F6h			
00F7h			
00F8h			
00F9h			
00FAh			
00FBh			
00FCh			
00FDh			
00FEh			
00FFh			
00E0h	Port P4 Register	P4	XXh
00E1h			
00E2h			
00E3h			
00E4h			
00E5h			
00E6h			
00E7h			
00E8h			
00E9h			
00EAh			
00EBh			
00ECh			
00EDh			
00EEh			
00EFh			
00F0h	Port P4 Direction Register	PD4	00h
00F1h			
00F2h			
00F3h			
00F4h			
00F5h			
00F6h			
00F7h			
00F8h			
00F9h			
00FAh			
00FBh			
00FCh			
00FDh			
00FEh			
00FFh			
00FCh	Pull-Up Control Register 0	PUR0	00XX0000b
00FDh		PUR1	XXXXXX0Xb
00FEh	Port P1 Drive Capacity Control Register	DRR	00h
00FFh	Timer C Output Control Register	TCOUT	00h
01B3h	Flash Memory Control Register 4	FMR4	01000000b
01B4h	Flash Memory Control Register 1	FMR1	1000000Xb
01B5h			
01B6h	Flash Memory Control Register 0	FMR0	00000001b
01B7h			
0FFFFh	Optional Function Select Register	OFS	(Note 2)

X: Undefined

NOTES:

1. The blank regions, 0100h to 01B2h and 01B8h to 02FFh are all reserved. Do not access locations in these regions.
2. The OFS register cannot be changed by a program. Use a flash programmer to write to it.

Table 5.4 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
—	Program/erase endurance ⁽²⁾	R8C/18 Group	100 ⁽³⁾	—	—	times
		R8C/19 Group	1,000 ⁽³⁾	—	—	times
—	Byte program time		—	50	400	μs
—	Block erase time		—	0.4	9	s
t _d (SR-SUS)	Time delay from suspend request until suspend		—	—	97+CPU clock × 6 cycles	μs
—	Interval from erase start/restart until following suspend request		650	—	—	μs
—	Interval from program start/restart until following suspend request		0	—	—	ns
—	Time from suspend until program/erase restart		—	—	3+CPU clock × 4 cycles	μs
—	Program, erase voltage		2.7	—	5.5	V
—	Read voltage		2.7	—	5.5	V
—	Program, erase temperature		0	—	60	°C
—	Data hold time ⁽⁸⁾	Ambient temperature = 55 °C	20	—	—	year

NOTES:

1. V_{CC} = 2.7 to 5.5 V at T_{opr} = 0 to 60 °C, unless otherwise specified.
2. Definition of programming/erasure endurance
The programming and erasure endurance is defined on a per-block basis.
If the programming and erasure endurance is n (n = 100 or 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. If emergency processing is required, a suspend request can be generated independent of this characteristic. In that case the normal time delay to Suspend can be applied to the request. However, we recommend that a suspend request with an interval of less than 650 μs is only used once because, if the suspend state continues, erasure cannot operate and the incidence of erasure error rises.
5. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the number of erase operations between block A and block B can further reduce the effective number of rewrites. It is also advisable to retain data on the erase count of each block and limit the number of erase operations to a certain number.
6. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
7. Customers desiring programming/erasure failure rate information should contact their Renesas technical support representative.
8. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.5 Flash Memory (Data flash Block A, Block B) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance ⁽²⁾		10,000 ⁽³⁾	–	–	times
–	Byte program time (Program/erase endurance ≤ 1,000 times)		–	50	400	μs
–	Byte program time (Program/erase endurance > 1,000 times)		–	65	–	μs
–	Block erase time (Program/erase endurance ≤ 1,000 times)		–	0.2	9	s
–	Block erase time (Program/erase endurance > 1,000 times)		–	0.3	–	s
t _d (SR-SUS)	Time delay from suspend request until suspend		–	–	97+CPU clock × 6 cycles	μs
–	Interval from erase start/restart until following suspend request		650	–	–	μs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3+CPU clock × 4 cycles	μs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.7	–	5.5	V
–	Program, erase temperature		-20 ⁽⁸⁾	–	85	°C
–	Data hold time ⁽⁹⁾	Ambient temperature = 55 °C	20	–	–	year

NOTES:

1. V_{CC} = 2.7 to 5.5 V at T_{opr} = -20 to 85 °C / -40 to 85 °C, unless otherwise specified.
2. Definition of programming/erasure endurance
The programming and erasure endurance is defined on a per-block basis.
If the programming and erasure endurance is n (n = 100 or 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. If emergency processing is required, a suspend request can be generated independent of this characteristic. In that case the normal time delay to suspend can be applied to the request. However, we recommend that a suspend request with an interval of less than 650 μs is only used once because, if the suspend state continues, erasure cannot operate and the incidence of erasure error rises.
5. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erase count of each block and limit the number of erase operations to a certain number.
6. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
7. Customers desiring programming/erasure failure rate information should contact their Renesas technical support representative.
8. -40 °C for D version.
9. The data hold time includes time that the power supply is off or the clock is not supplied.

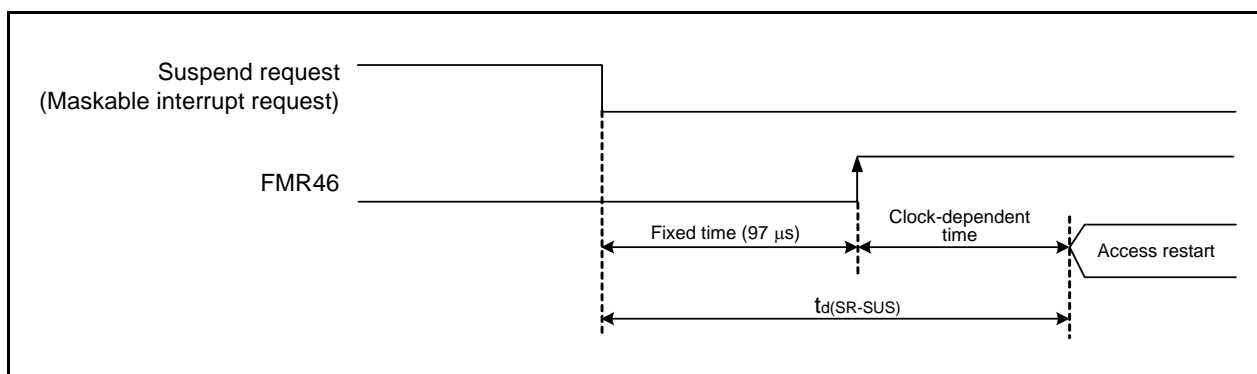
**Figure 5.2 Transition Time to Suspend**

Table 5.6 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V _{det1}	Voltage detection level ⁽³⁾		2.70	2.85	3.00	V
—	Voltage detection circuit self power consumption	VCA26 = 1, V _{CC} = 5.0 V	—	600	—	nA
t _{d(E-A)}	Waiting time until voltage detection circuit operation starts ⁽²⁾		—	—	100	μs
V _{ccmin}	MCU operating voltage minimum value		2.7	—	—	V

NOTES:

1. The measurement condition is V_{CC} = 2.7 V to 5.5 V and T_{opr} = -40°C to 85 °C.
2. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.
3. Ensure that V_{det2} > V_{det1}.

Table 5.7 Voltage Detection 2 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V _{det2}	Voltage detection level ⁽⁴⁾		3.00	3.30	3.60	V
—	Voltage monitor 2 interrupt request generation time ⁽²⁾		—	40	—	μs
—	Voltage detection circuit self power consumption	VCA27 = 1, V _{CC} = 5.0 V	—	600	—	nA
t _{d(E-A)}	Waiting time until voltage detection circuit operation starts ⁽³⁾		—	—	100	μs

NOTES:

1. The measurement condition is V_{CC} = 2.7 V to 5.5 V and T_{opr} = -40°C to 85 °C.
2. Time until the voltage monitor 2 interrupt request is generated after the voltage passes V_{det1}.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.
4. Ensure that V_{det2} > V_{det1}.

Table 5.8 Reset Circuit Electrical Characteristics (When Using Voltage Monitor 1 Reset)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V _{por2}	Power-on reset valid voltage	-20°C ≤ Topr ≤ 85°C	—	—	V _{det1}	V
t _w (V _{por2} -V _{det1})	Supply voltage rising time when power-on reset is deasserted ⁽¹⁾	-20°C ≤ Topr ≤ 85°C, t _w (por2) ≥ 0s ⁽³⁾	—	—	100	ms

NOTES:

1. This condition is not applicable when using with V_{cc} ≥ 1.0 V.
2. When turning power on after the time to hold the external power below effective voltage (V_{por1}) exceeds 10 s, refer to **Table 5.9 Reset Circuit Electrical Characteristics (When Not Using Voltage Monitor 1 Reset)**.
3. t_w(por2) is the time to hold the external power below effective voltage (V_{por2}).

Table 5.9 Reset Circuit Electrical Characteristics (When Not Using Voltage Monitor 1 Reset)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V _{por1}	Power-on reset valid voltage	-20°C ≤ Topr ≤ 85°C	—	—	0.1	V
t _w (V _{por1} -V _{det1})	Supply voltage rising time when power-on reset is deasserted	0°C ≤ Topr ≤ 85°C, t _w (por1) ≥ 10 s ⁽²⁾	—	—	100	ms
t _w (V _{por1} -V _{det1})	Supply voltage rising time when power-on reset is deasserted	-20°C ≤ Topr < 0°C, t _w (por1) ≥ 30 s ⁽²⁾	—	—	100	ms
t _w (V _{por1} -V _{det1})	Supply voltage rising time when power-on reset is deasserted	-20°C ≤ Topr < 0°C, t _w (por1) ≥ 10 s ⁽²⁾	—	—	1	ms
t _w (V _{por1} -V _{det1})	Supply voltage rising time when power-on reset is deasserted	0°C ≤ Topr ≤ 85°C, t _w (por1) ≥ 1 s ⁽²⁾	—	—	0.5	ms

NOTES:

1. When not using voltage monitor 1, use with V_{cc} ≥ 2.7 V.
2. t_w(por1) is the time to hold the external power below effective voltage (V_{por1}).

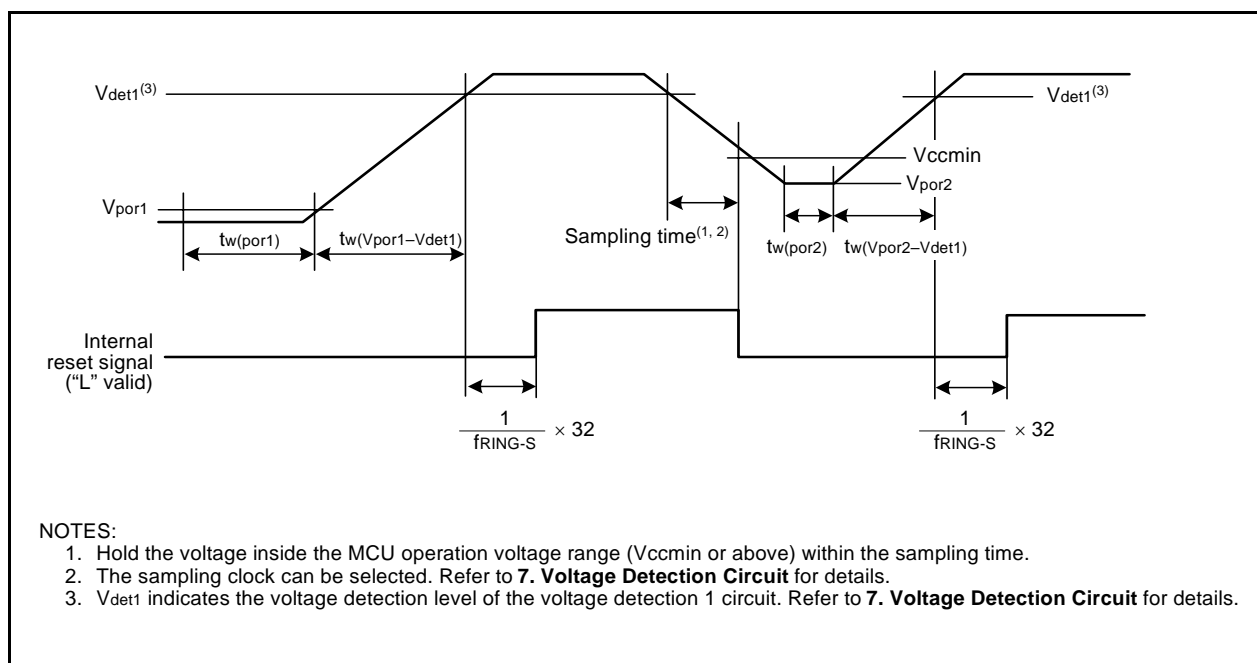
**Figure 5.3 Reset Circuit Electrical Characteristics**

Table 5.12 Electrical Characteristics (1) [V_{CC} = 5 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V _{OH}	Output "H" voltage	Except X _{OUT}	I _{OH} = -5 mA		V _{CC} - 2.0	—	V _{CC}	V
			I _{OH} = -200 μA		V _{CC} - 0.3	—	V _{CC}	V
		X _{OUT}	Drive capacity HIGH	I _{OH} = -1 mA	V _{CC} - 2.0	—	V _{CC}	V
			Drive capacity LOW	I _{OH} = -500 μA	V _{CC} - 2.0	—	V _{CC}	V
V _{OL}	Output "L" voltage	Except P1_0 to P1_3, X _{OUT}	I _{OL} = 5 mA		—	—	2.0	V
			I _{OL} = 200 μA		—	—	0.45	V
		P1_0 to P1_3	Drive capacity HIGH	I _{OL} = 15 mA	—	—	2.0	V
			Drive capacity LOW	I _{OL} = 5 mA	—	—	2.0	V
			Drive capacity LOW	I _{OL} = 200 μA	—	—	0.45	V
		X _{OUT}	Drive capacity HIGH	I _{OL} = 1 mA	—	—	2.0	V
			Drive capacity LOW	I _{OL} = 500 μA	—	—	2.0	V
V _{T+} -V _{T-}	Hysteresis	INT0, INT1, INT2, INT3, KI0, KI1, KI2, KI3, CNTR0, CNTR1, TCIN, RXD0			0.2	—	1.0	V
		RESET			0.2	—	2.2	V
I _{IH}	Input "H" current		V _I = 5 V		—	—	5.0	μA
I _{IL}	Input "L" current		V _I = 0 V		—	—	-5.0	μA
R _{PULLUP}	Pull-up resistance		V _I = 0 V		30	50	167	kΩ
R _{FXIN}	Feedback resistance	XIN			—	1.0	—	MΩ
f _{RING-S}	Low-speed on-chip oscillator frequency				40	125	250	kHz
V _{RAM}	RAM hold voltage		During stop mode		2.0	—	—	V

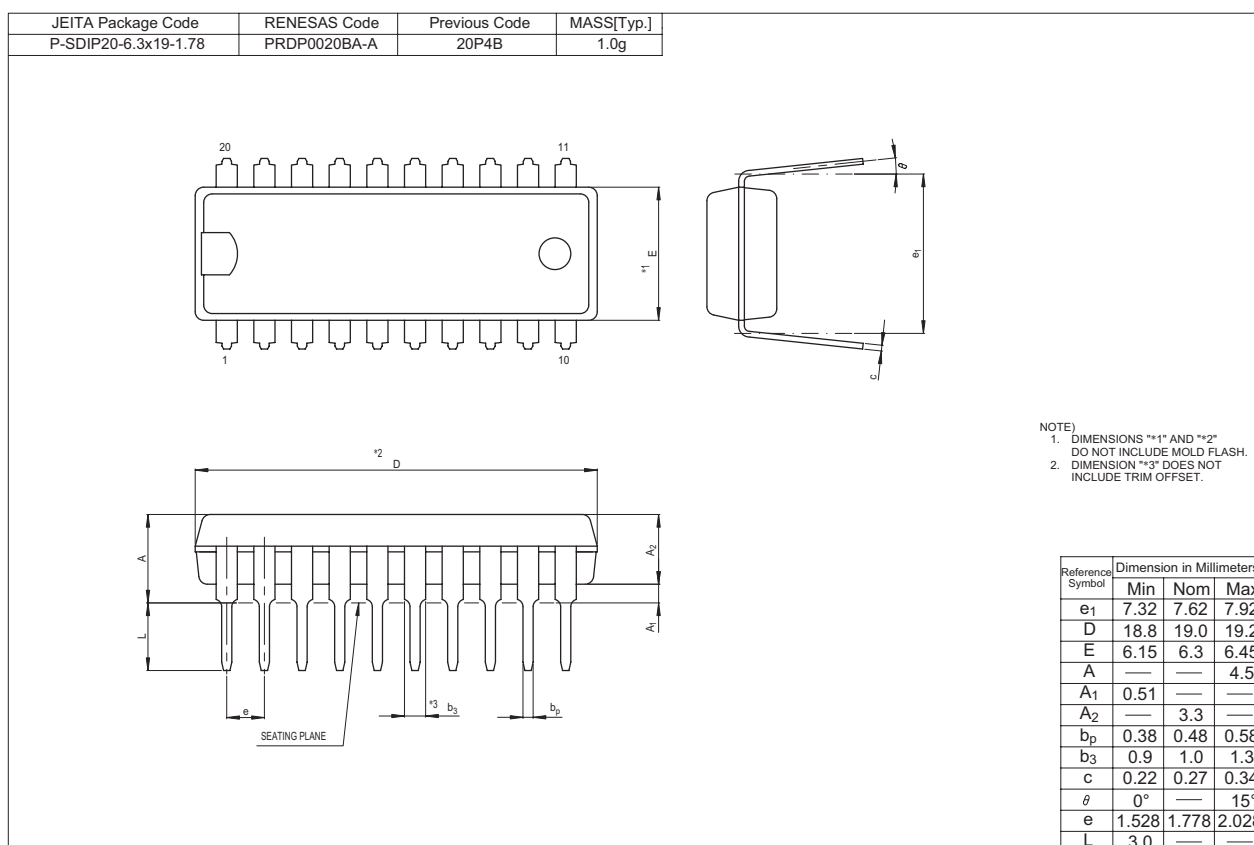
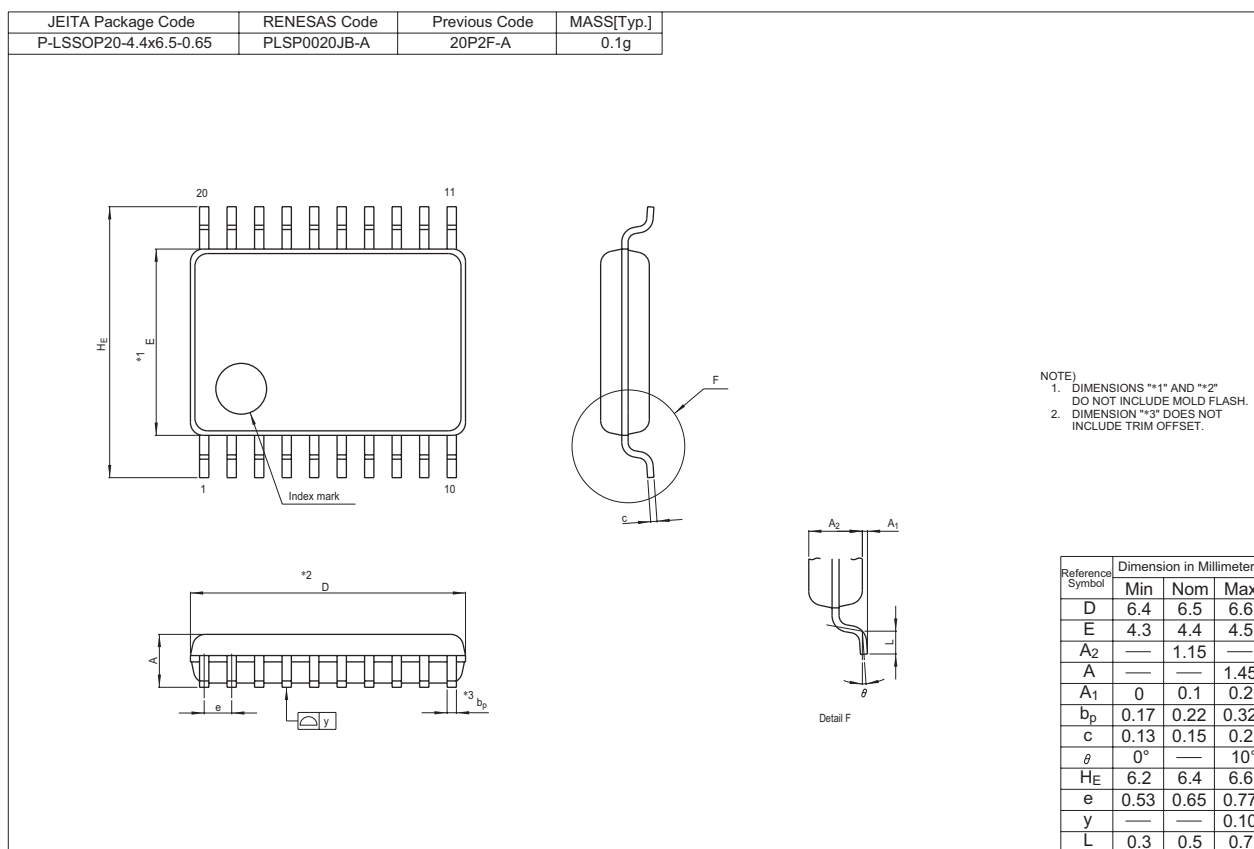
NOTE:

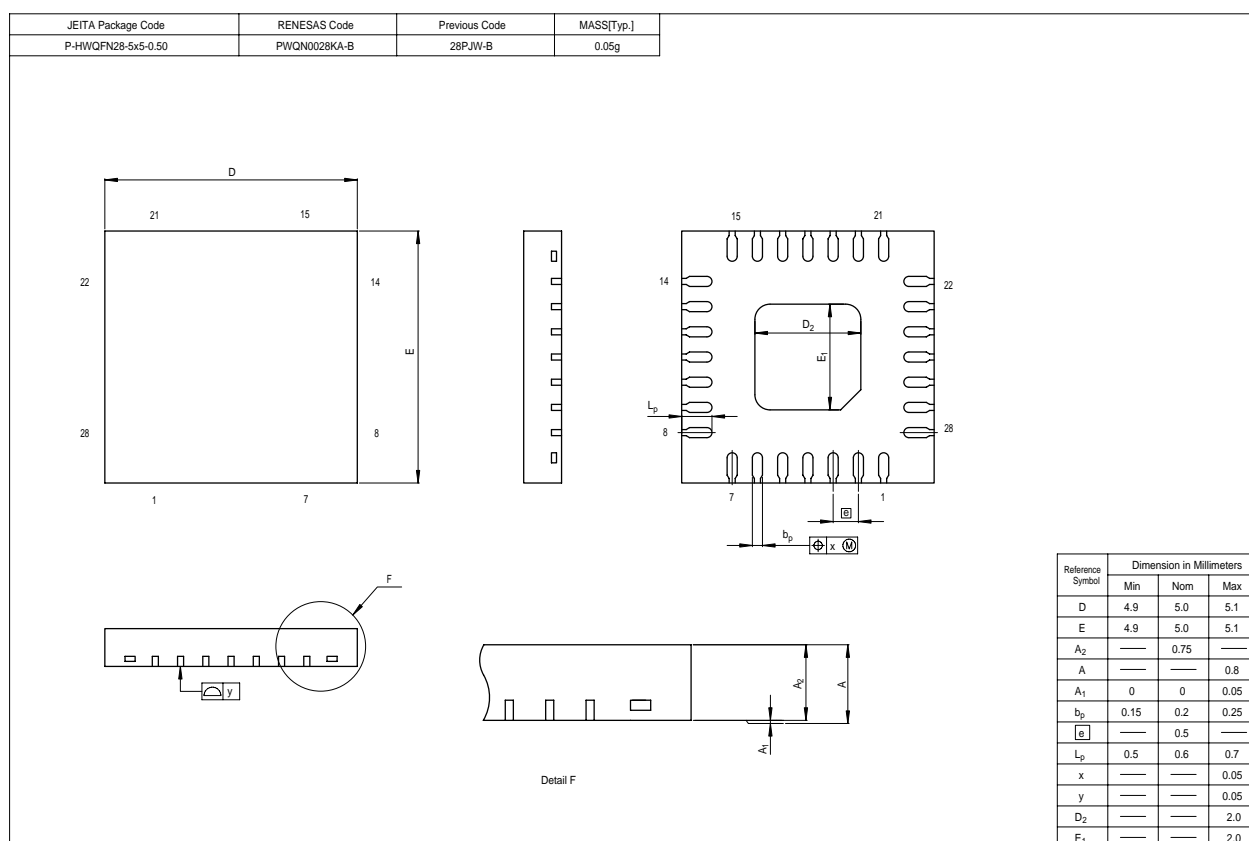
1. V_{CC} = 4.2 to 5.5 V at T_{opr} = -20 to 85 °C / -40 to 85 °C, f(XIN) = 20 MHz, unless otherwise specified.

Table 5.13 Electrical Characteristics (2) [Vcc = 5 V] (Topr = -40 to 85 °C, unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
Icc	Power supply current (Vcc = 3.3 to 5.5 V) Single-chip mode, output pins are open, other pins are Vss, comparator is stopped	High-speed mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	9	15	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	8	14	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	5	–	mA
		Medium-speed mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	4	–	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	3	–	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2	–	mA
		High-speed on-chip oscillator mode	Main clock off High-speed on-chip oscillator on = 8 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	4	8	mA
			Main clock off High-speed on-chip oscillator on = 8 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	–	mA
		Low-speed on-chip oscillator mode	Main clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8 FMR47 = 1	–	110	300	μA
		Wait mode	Main clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = 0	–	40	80	μA
		Wait mode	Main clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = 0	–	38	76	μA
		Stop mode	Main clock off, Topr = 25 °C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = 0	–	0.8	3.0	μA

Package Dimensions





REVISION HISTORY	R8C/18 Group, R8C/19 Group Datasheet
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Rev.	Date	Description	
		Page	Summary
0.10	Nov 15, 2004	–	First Edition issued
0.20	Jan 11, 2005	5, 6	Tables 1.3 and 1.4: The date updated
0.21	Apr 04, 2005	2, 3 4 5, 6 5, 6 7, 8 10 16 17 18 20	Tables 1.1 and 1.2: Partly revised Figure 1.1: Partly revised Tables 1.3 and 1.4: Partly revised Figure 1.2 and 1.3: Partly revised Figure 1.4 and 1.5: Partly revised Table 1.6: Partly revised Table 4.1: Partly revised Table 4.2: Partly revised Table 4.3: Partly revised Package Dimensions are revised
1.00	May 27, 2005	5, 6 9 25 26 28 32	Tables 1.3 and 1.4: Partly revised Table 1.5: Partly revised Table 5.9: Revised Table 5.10: Partly revised Table 5.13: Partly revised Table 5.20: Partly revised
1.10	Jun 09, 2005	26	Table 5.10: Partly revised
1.20	Nov 01, 2005	3 4 6 9 11 13 15	Table 1.2 Performance Outline of the R8C/19 Group; Flash Memory: (Data area) → (Data flash) (Program area) → (Program ROM) revised Figure 1.1 Block Diagram; “Peripheral Function” added, “System Clock Generation” → “System Clock Generator” revised Table 1.4 Product Information of R8C/19 Group; ROM capacity: “Program area” → “Program ROM”, “Data area” → “Data flash” revised Table 1.5 Pin Description; Power Supply Input: “VCC/AVCC” → “VCC”, “VSS/AVSS” → “VSS” revised Analog Power Supply Input: added Figure 2.1 CPU Register; “Reserved Area” → “Reserved Bit” revised 2.8.10 Reserved Area; “Reserved Area” → “Reserved Bit” revised 3.2 R8C/19 Group, Figure 3.2 Memory Map of R8C/19 Group; “Data area” → “Data flash”, “Program area” → “Program ROM” revised

REVISION HISTORY		R8C/18 Group, R8C/19 Group Datasheet	
Rev.	Date	Description	
		Page	Summary
1.20	Nov 01, 2005	16	Table 4.1 SFR Information(1); 0009h: "XXXXXX00b" → "00h" 000Ah: "00XXX000b" → "00h" 001Eh: "XXXXX000b" → "00h" revised
		18	Table 4.3 SFR Information(3); 0085h: "Prescaler Z" → "Prescaler Z Register" 0086h: "Timer Z Secondary" → "Timer Z Secondary Register" 0087h: "Timer Z Primary" → "Timer Z Primary Register" 008Ch: "Prescaler X" → "Prescaler X Register" 008Dh: "Timer X" → "Timer X Register" 0090h, 0091h: "Timer C" → "Timer C Register" revised
		22	Table 5.4 Flash Memory (Program ROM) Electrical Characteristics; NOTES 3 and 5 revised, NOTE8 deleted
		23	Table 5.5 Flash Memory (Data flash Block A, Block B) Electrical Characteristics; NOTES 1 and 3 revised
		25	Table 5.8 Reset Circuit Electrical Characteristics (When Using Voltage Monitor 1 Reset); NOTE 2 revised
		26	Table 5.10 High-speed On-Chip Oscillator Circuit Electrical Characteristics; "High-Speed On-Chip Oscillator ..." → "High-Speed On-Chip Oscillator Frequency ..." revised NOTE 2, 3 added
		28	Table 5.13 Electrical Characteristics (2) [Vcc = 5V]; NOTE 1 deleted
		32	Table 5.20 Electrical Characteristics (4) [Vcc = 3V]; NOTE 1 deleted
1.30	Dec 16, 2005	–	Products of PWQN0028KA-B package included
		5, 6	Table 1.3, Table 1.4 revised
		24	Table 5.4 Flash Memory (Program ROM) Electrical Characteristics; Ta → Ambient temperature
		25	Table 5.5 Flash Memory (Data flash Block A, Block B) Electrical Characteristics; Ta → Ambient temperature
		30, 34	Table 5.13, Table 5.20; The title revised, Condition of Stop Mode added
		32, 36	Table 5.17, Table 5.24; td(C-Q) and tsu(D-C) revised
1.40	Apr 14, 2006	37, 38	Package Dimensions revised
		2, 3	Table 1.1, Table 1.2; Interrupts: Internal 8 → 10 sources,
		5, 6	Table 1.3, Table 1.4; Type No. added, deleted
		16, 17	Figure 3.1, Figure 3.2; Part Number added, deleted
		24, 25	Table 5.4, Table 5.5; Conditions: VCC = 5.0 V at Topr = 25 °C deleted